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-	42	clean\$3 and freez\$3 and sonic and wafer	USPAT;	2003/04/24 09:16
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-	6	sacrificial near3 coating and 134/\$.ccls.	USPAT;	2004/01/16 13:53
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_	158	semiconductor) and coat\$3 and (contaminate	USPAT; US-PGPUB;	2003/04/26 08:13
		clean\$3 adhere adhesive)	EPO; JPO; DERWENT;	
	1	curable near1 polymer and (wafer	IBM_TDB USPAT;	2003/04/26 08:13
	_	semiconductor) and coat\$3 and (contaminate	US-PGPUB;	2003/04/20 00:13
		clean\$3 adhere adhesive) and clean\$3.ti.	EPO; JPO;	
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_	1	curable nearl polymer and (wafer	IBM_TDB USPAT;	2003/04/26 08:14
		semiconductor) and coat\$3 and (contaminate	US-PGPUB;	2003/04/26 06:14
		clean\$3 adhere adhesive) and (removal	EPO; JPO;	
		clean\$3).ti.	DERWENT;	
	130	curable nearl polymer and (wafer	IBM_TDB USPAT;	2003/04/26 08:23
		semiconductor) and coat\$3 and (contaminate	US-PGPUB;	2003/04/20 00.23
		clean\$3 adhere adhesive) and (adhesive	EPO; JPO;	
		removal clean\$3).ti.	DERWENT;	
-	. 361	curable nearl polymer and (face skin	IBM_TDB USPAT;	2003/04/26 08:24
		pore) and coat\$3 and (contaminate clean\$3	US-PGPUB;	2000, 01, 20 00.21
		adhere adhesive)	EPO; JPO;	,
			DERWENT; IBM TDB	
-	361	curable nearl polymer and (face skin	USPAT;	2003/04/26 08:30
		pore) and coat\$3 and (contaminate clean\$3	US-PGPUB;	2000, 51, 20 00 1,00
		adhere adhesive) and (adhesive removal	EPO; JPO;	
		clean\$3 skin face pore).ti.	DERWENT; IBM TDB	
- 7	0	curable near1 polymer and (face skin	USPAT;	2003/04/26 08:31
]		pore) and coat\$3 and (contaminate clean\$3	US-PGPUB;	.,,
		adhere adhesive) and (adhesive removal	EPO; JPO;	
		clean\$3 skin face pore).ti. and pore near2 cleaning	DERWENT; IBM TDB	
-	0	curable near1 polymer and pore near2	USPAT;	2003/04/26 08:31
		cleaning	US-PGPUB;	
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-	84	pore near2 cleaning	USPAT;	2003/04/26 08:44
			US-PGPUB;	
			EPO; JPO; DERWENT;	
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-	2	pore near2 cleaning and (polyimide lacquer	USPAT;	2003/04/26 08:47
		latex rubber hearl cement)	US-PGPUB;	
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-	3684	polyimide and adhesive and cleaning	USPAT;	2003/04/26 08:47
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-	3684	polyimide and adhesive and cleaning sacrificail and coating	USPAT;	2003/04/26 08:48
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	244	sacrificial and coating	USPAT; US-PGPUB;	2003/04/26 08:48
			EPO; JPO;	
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_	244	polyimide and adhesive and cleaning and	IBM_TDB	2002/04/26 22 42
	244	sacrificial and coating and surface	USPAT; US-PGPUB;	2003/04/26 08:48
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-	18	polyimide and adhesive and cleaning and	USPAT;	2003/04/26 08:49
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-	1	"3063873".PN.	USPAT	2003/04/26 09:36
-	1	"3079284".PN.	USPAT	2003/04/26 09:36
-	1	"3404134".PN.	USPAT	2003/04/26 09:36
-	1	"3634278".PN.	USPAT	2003/04/26 09:36
-	1	"4053666".PN.	USPAT	2003/04/26 09:36
_	2	"20020189635"	USPAT;	2003/04/26 09:50
		•	US-PGPUB;	2003/04/20 09:30
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-	38370	sonic near5 clean\$3 and dislodge near6	USPAT;	2003/04/26 10:03
1		particulate matter and polymer and layer	US-PGPUB;	
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_	0	sonic near5 clean\$3 and dislodge near6	USPAT;	2003/04/26 10:03
		particulate near3 matter and polymer and	US-PGPUB:	2003/04/20 10:03
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	İ	sacrificial near3 (coating layer polymer)	US-PGPUB;	
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i			US-PGPUB;	2003/03/10 03:39
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-	1	"3080263".PN.	USPAT	2003/09/18 09:35
-	1	"3717897".PN.	USPAT	2003/09/18 09:37
-	1	"3754991".PN.	USPAT	2003/09/18 09:37
-	1	"4156619".PN.	USPAT	2003/09/18 09:37
-	1	"5320706".PN.	USPAT	2003/09/18 09:37
-	573	strippable near2 coating	USPAT;	
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16 Strippable near2 coating and contaminant US_PATT US_PGUUS; ENG JPC; DEWNERD; ENG JPC; DEWNE					
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30 ultrasonic near33 encapsulat\$4 and wafer USPAT; USPGUB; EPO; JPO; DERWENT; IBM TOB USPAT; US-FGFUB; EPO; JPO; DERWENT; IBM TOB USPAT USPAT USPAT 2003/09/18 13:41 2003/09/18 13:41 2003/09/18 13:41 2003/09/18 13:41 2003/09/18 13:42 2003/09/18 13:41 2003/09/18 13:42 2003/09/18 13:41 2003					
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B07 encapsulat\$4 with contaminant EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT		10300	cheapsulate and contaminant		2003/09/18 10:55
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106 encapsulat\$4 with contaminant and (sonic ultrasonic megasonic) US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT 2003/09/18 13:41					
106 encapsulat\$4 with contaminant and (sonic ultrasonic megasonic) EPO; JPO; DERWENT; TBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; TBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; TBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; TBM TDB USPAT uspart 2003/09/18 11:27 USPAT 2003/09/18 13:41 USPAT 2003/09/18 13:41 USPAT 2003/09/18 13:41 USPAT 2003/09/18 13:41 USPAT 2003/09/18 13:42 USPAT 2003/09/18 13:42 USPAT 2003/09/18 13:42 USPAT 2003/09/18 13:45 USPAT 2003/09/18 13:45 USPAT; USPAT 2003/09/18 13:45 USPAT;	_	807	encapsulat\$4 with contaminant		2003/09/18 10:55
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-	1	"3419427".PN.	USPAT	2003/09/18 18:24
_	1	"3733710".PN.	USPAT	2003/09/18 18:24
-	1	"4186032".PN.	USPAT	2003/09/18 18:24
-	1	"4266982".PN.	USPAT	2003/09/18 18:24
-	1	"4409034".PN.	USPAT	2003/09/18 18:24
-	1	"4586962".PN.	USPAT	2003/09/18 18:24
-	. 1	"4622075".PN.	USPAT	2003/09/18 18:24
-	1	"4628616".PN.	USPAT	2003/09/18 18:24
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